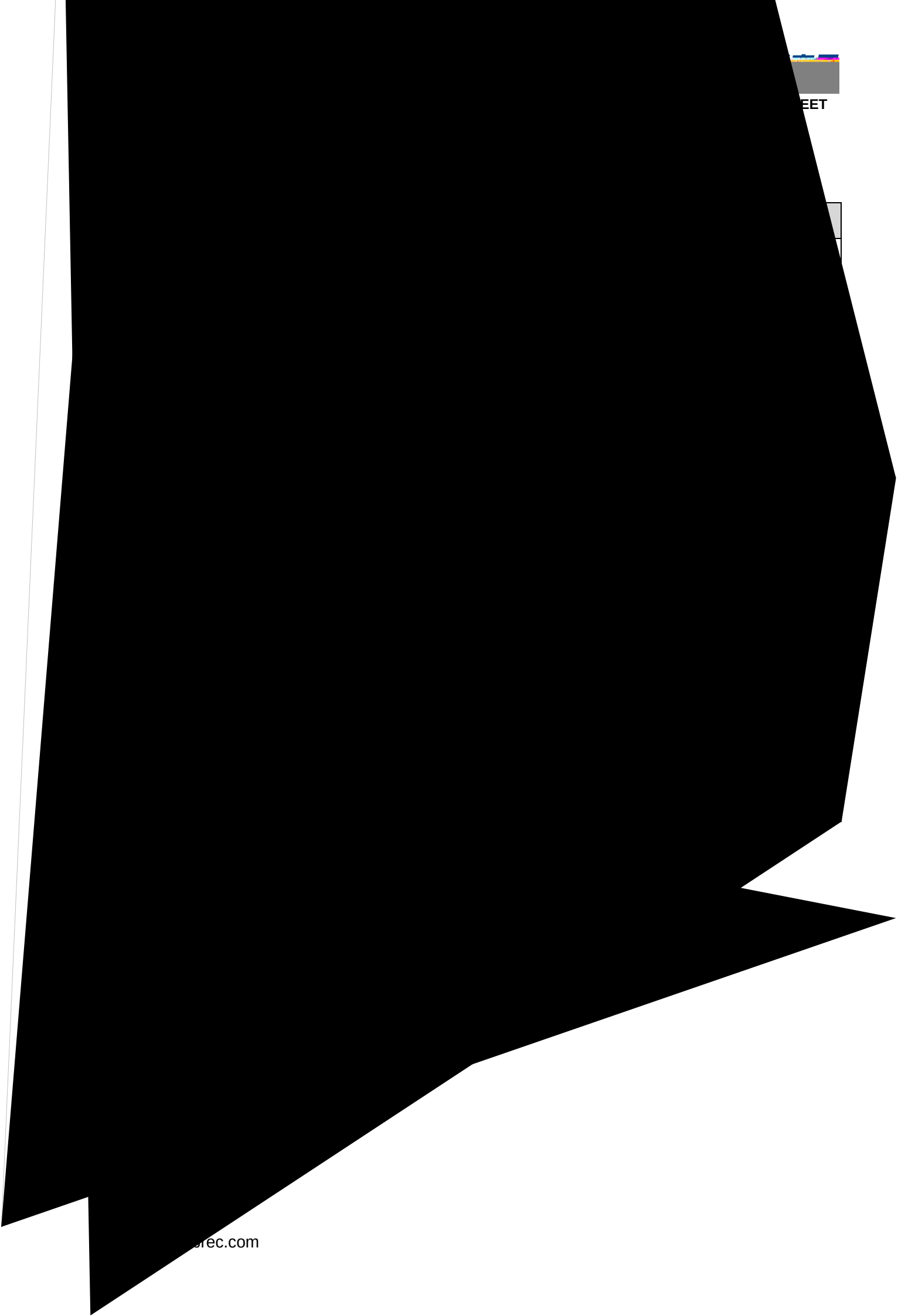

EET

SOP-8 MOS

Complementary Enhancement MOSFET in a SOP-8 Plastic Package.

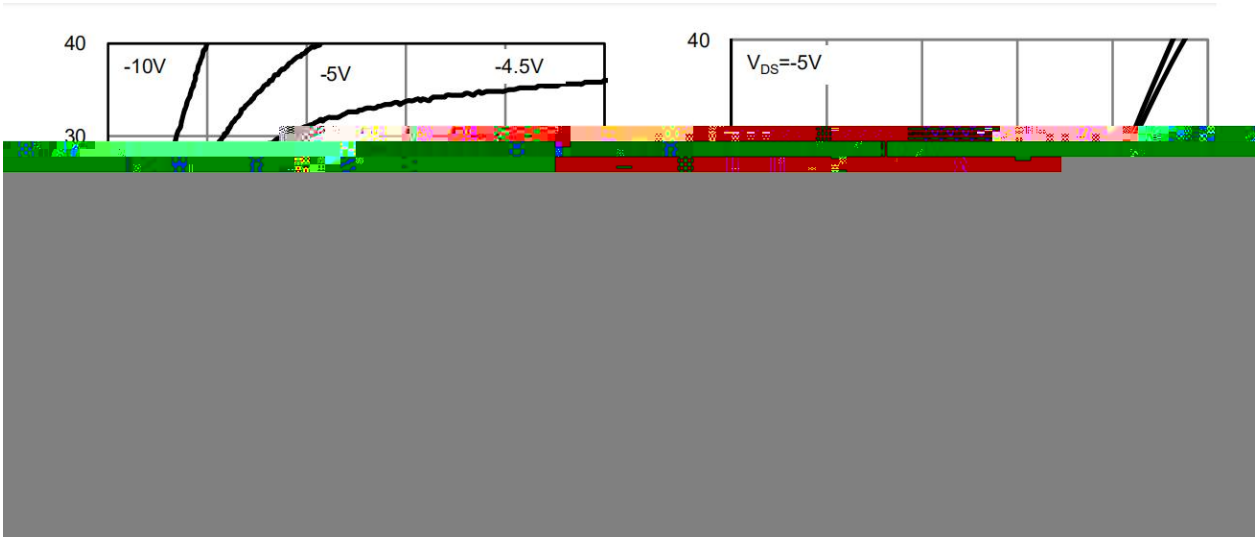
N-channel	P-channel
V_{DS}(V)=30V	V_{DS}(V)=-30V
I_D=6.9A	I_D=-6.0A
$R_{DS(ON)}$<32m Ω (V_{GS}=10V)	$R_{DS(ON)}$<70m Ω (V_{GS}=-10V)
$R_{DS(ON)}$<40m Ω (V_{GS}=4.5V)	$R_{DS(ON)}$<90m Ω (V_{GS}=-4.5V)

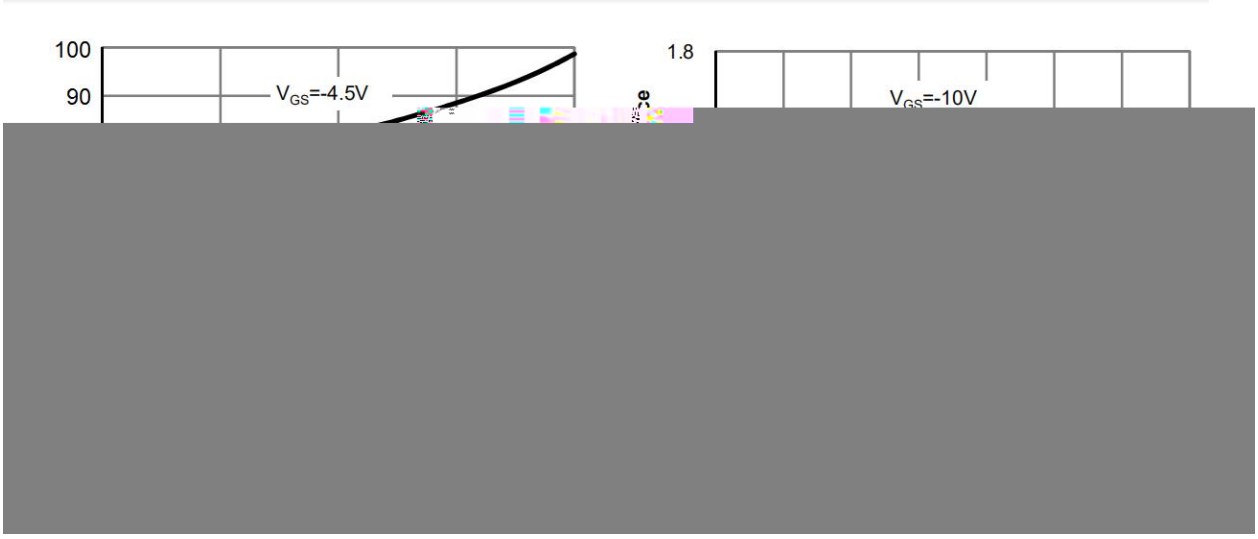
BRCS4606HSC
Rev.B Mar.-a

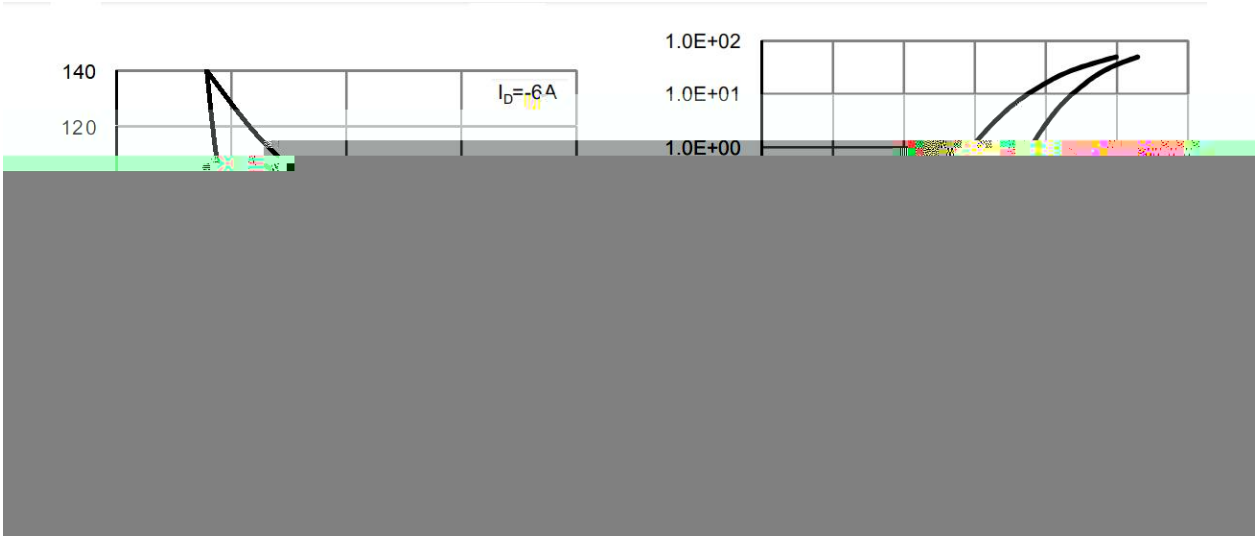
Paramet/ n

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-30	-33.8		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V V_{GS}=0V			-1.0	μA
		V_{DS}=-24V V_{GS}=0V T_J=55℃			-5.0	μA
Gate-Body leakage current	I_{GSS}	V_{GS}=±20V V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=-250μA	-1.3	-1.85	-2.4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V I_D=-6.0A		50.3	70	mΩ
		V_{GS}=-4.5V I_D=-5.0A		79.4	90	mΩ
Diode Forward Voltage	V_{SD}	V_{GS}=0V I_S=-1.0A		-0.81	-1.0	V
Input Capacitance	C_{iss}	V_{DS}=-25V V_{GS}=0V f=1.0MHz		465		pF
Output Capacitance	C_{oss}			150		pF
Reverse Transfer Capacitance	C_{rss}			40		pF
Gate resistance	R_g	V_{DS}=0V V_{GS}=0V f=1.0MHz		5.5		Ω
Total Gate Charge(10V)	Q_g	V_{GS}≠g				

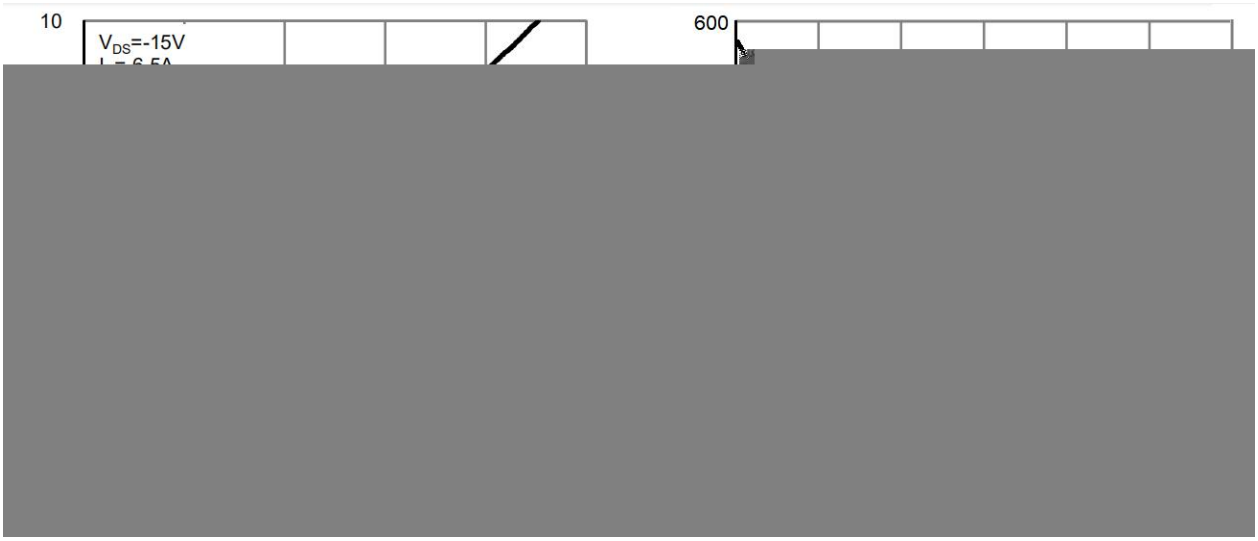
P– / P-CHANNEL Electrical Characteristic Curve

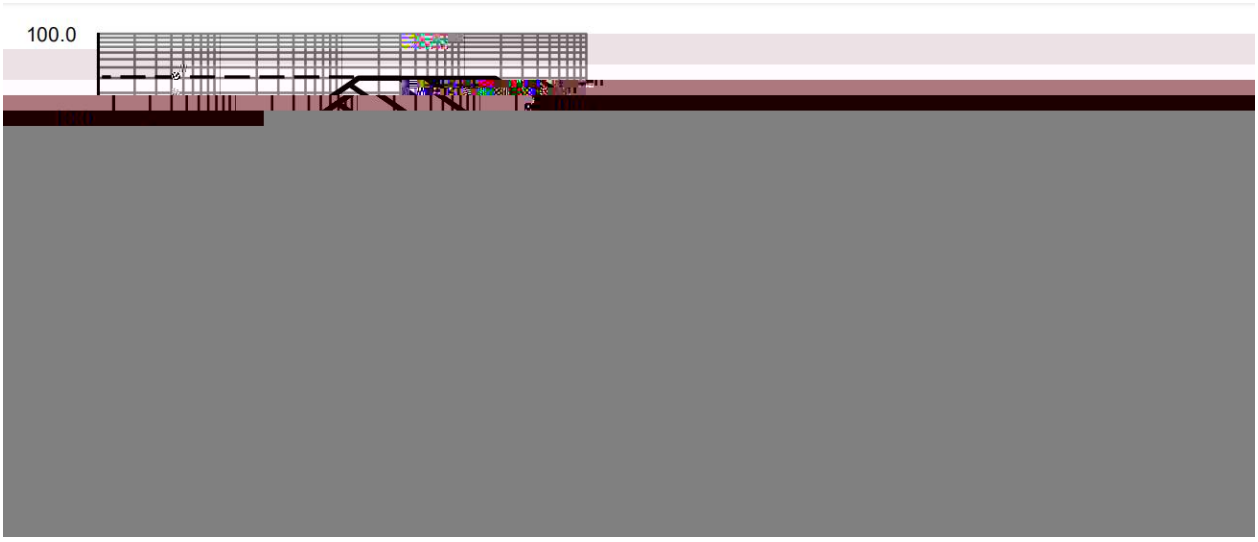


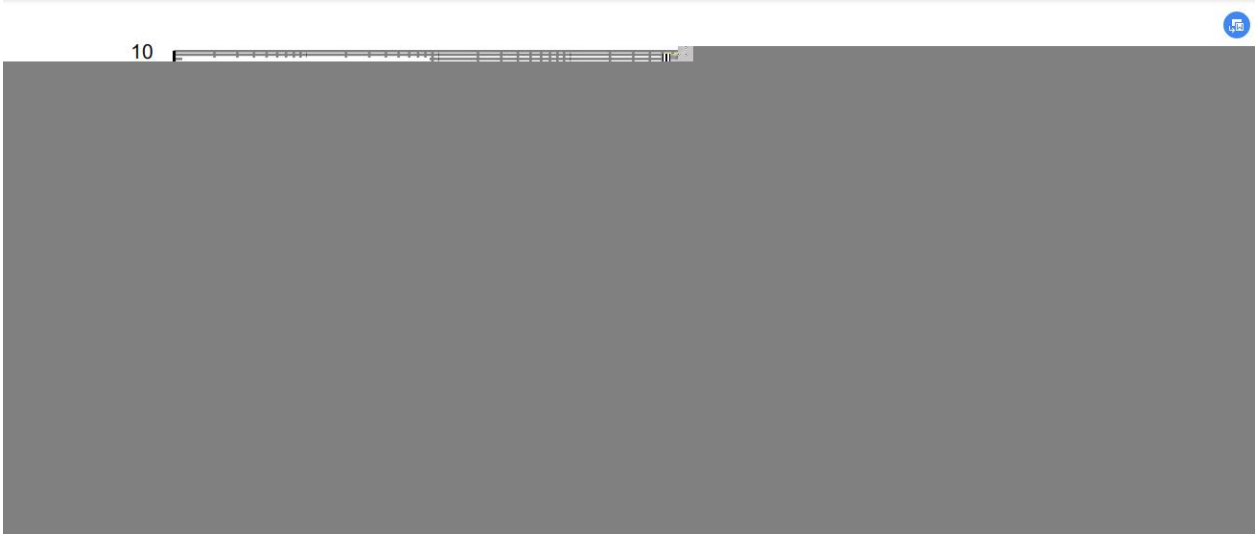




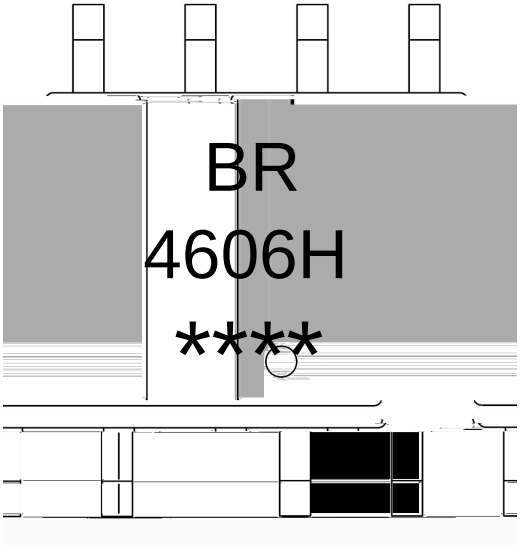
P– / P-CHANNEL Electrical Characteristic Curve







/ Marking Instructions



BR

4606H

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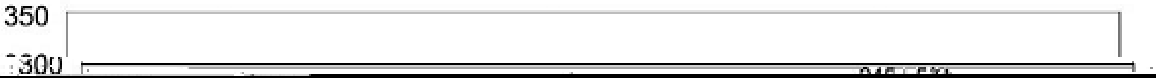
Note:

BR:	Company Code.
4606H:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



[redacted]

Note:

1	150 180	60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5	5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3		2 10 /sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±2/5	10±1 sec.	Temp.:260±5	Time:10±1 sec

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